

Abstract

A method for producing a semiconductor integrated circuit device, and a semiconductor integrated circuit device are disclosed. In the method, a first select gate electrode (G2a, G2b) and a second select gate electrode (G3a, G3b) electrically insulated from each other are formed in a memory circuit region (ER1) through a photomask process of forming a logic gate electrode (G5, G6) in a peripheral circuit region (ER2). Thus, even when the first select gate electrode (G2a or G2b) and the second select gate electrode (G3a, G3b) are formed to be separately controllable, an extra dedicated photomask process of fabricating only the memory circuit region (ER1) does not need to be performed in addition to a conventional dedicated photomask process of fabricating only a memory circuit region. Thereby, production cost is reduced accordingly.